General Purpose Transistors

PNP Silicon

Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V_{CEO}	-45	V
Collector – Base Voltage	V_{CBO}	-50	V
Emitter – Base Voltage	V_{EBO}	-5.0	V
Collector Current – Continuous	I _C	-500	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (Note 1) T _A = 25°C Derate above 25°C	P _D	225 1.8	mW mW/°C
Thermal Resistance, Junction–to–Ambient (Note 1)	$R_{\theta JA}$	436	°C/W
Total Device Dissipation Alumina Substrate, (Note 1) T _A = 25°C Derate above 25°C	P _D	300 2.4	mW mW/°C
Thermal Resistance, Junction–to–Ambient (Note 2)	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

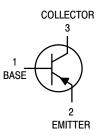
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. FR-4 Board, 1 oz. Cu, 100mm².
- Alumina = 0.4 x 0.3 x 0.024 in 99.5% alumina.



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SOT-23 CASE 318 STYLE 6

MARKING DIAGRAM



5xx = Device Code xx = A1, B1, or C $M = Date Code^*$

= Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Тур	Max	Unit	
OFF CHARACTERISTICS						
Collector – Emitter Breakdown Voltage (I _C = -10 mA)		V _{(BR)CEO}	-45	-	-	V
Collector – Emitter Breakdown Voltage $(V_{EB} = 0, I_C = -10 \mu A)$		V _(BR) CES	-50	-	-	V
Emitter – Base Breakdown Voltage ($I_E = -1.0 \mu A$)		V _{(BR)EBO}	-5.0	-	-	V
Collector Cutoff Current $(V_{CB} = -20 \text{ V})$ $(V_{CB} = -20 \text{ V}, T_{J} = 150^{\circ}\text{C})$		ІСВО	_ _	- -	-100 -5.0	nA μA
ON CHARACTERISTICS						
DC Current Gain $(I_C = -100 \text{ mA}, V_{CE} = -1.0 \text{ V})$ $(I_C = -500 \text{ mA}, V_{CE} = -1.0 \text{ V})$	BC807-16, SBC80-16L BC807-25, SBC807-25L BC807-40, SBC807-40L	h _{FE}	100 160 250 40	- - -	250 400 600 –	-
Collector – Emitter Saturation Voltage (I _C = -500 mA, I _B = -50 mA)		V _{CE(sat)}	-	-	-0.7	V
Base – Emitter On Voltage (I _C = –500 mA, V _{CE} = –1.0 V)		V _{BE(on)}	-	-	-1.2	V
SMALL-SIGNAL CHARACTERISTICS			-	•		
Current – Gain – Bandwidth Product $(I_C = -10 \text{ mA}, V_{CE} = -5.0 \text{ Vdc}, f = 100 \text{ MHz})$)	f _T	100	-	-	MHz
Output Capacitance $(V_{CB} = -10 \text{ V}, f = 1.0 \text{ MHz})$		C _{obo}	-	10	-	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

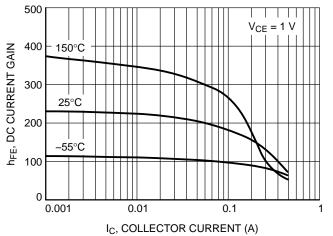
ORDERING INFORMATION

Device	Specific Marking	Package	Shipping [†]
BC807-16LT1G	504		2000 / Tarra & David
SBC807-16LT1G*	5A1		3000 / Tape & Reel
BC807-16LT3G	5A1		40,000 / Tana & Daal
SBC807-16LT3G*	5A1		10,000 / Tape & Reel
BC807-25LT1G	5D4		2000 / Tono & Dool
SBC807-25LT1G*	5B1	SOT-23	3000 / Tape & Reel
BC807-25LT3G	5B1	(Pb-Free)	40,000 / Tana & Baal
SBC807-25LT3G*	351		10,000 / Tape & Reel
BC807-40LT1G	5C		2000 / Tono & Dool
SBC807-40LT1G*			3000 / Tape & Reel
BC807-40LT3G	5C		10 000 / Tone & Reel
SBC807-40LT3G*	50		10,000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging

Specifications Brochure, BRD8011/D.
*S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable.

TYPICAL CHARACTERISTICS - BC807-16LT1

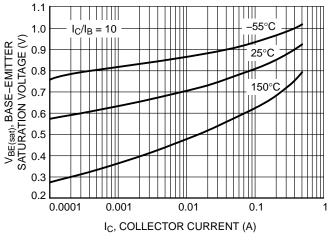


VCE(sat), COLLECTOR-EMITTER SATURATION VOLTAGE (V) 150°C 25°C 0.01 0.001 0.01 0.1 IC, COLLECTOR CURRENT (A)

 $I_{\rm C}/I_{\rm B} = 10$

Figure 1. DC Current Gain vs. Collector Current

Figure 2. Collector Emitter Saturation Voltage vs. Collector Current



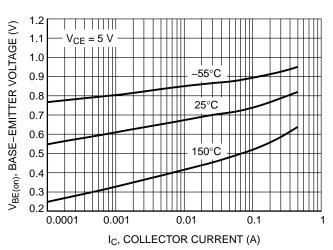


Figure 3. Base Emitter Saturation Voltage vs. **Collector Current**

Figure 4. Base Emitter Voltage vs. Collector Current

TYPICAL CHARACTERISTICS - BC807-16LT1

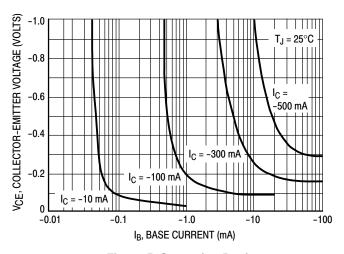


Figure 5. Saturation Region

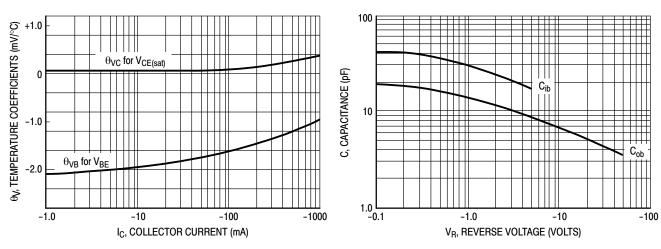


Figure 6. Temperature Coefficients

Figure 7. Capacitances

TYPICAL CHARACTERISTICS - BC807-25LT1

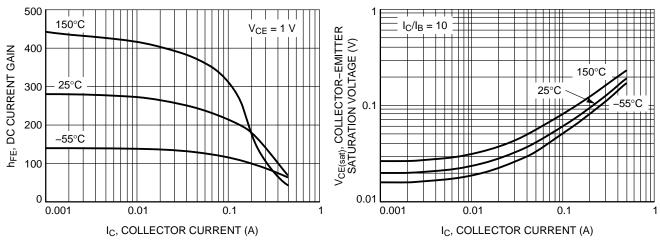


Figure 8. DC Current Gain vs. Collector Current

Figure 9. Collector Emitter Saturation Voltage vs. Collector Current

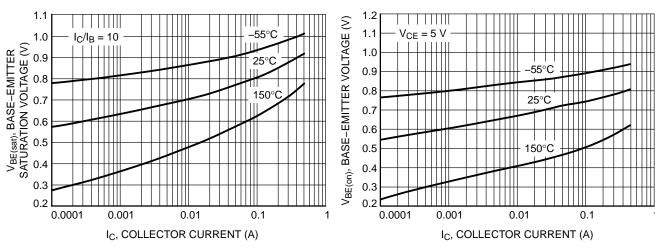


Figure 10. Base Emitter Saturation Voltage vs.
Collector Current

Figure 11. Base Emitter Voltage vs. Collector Current

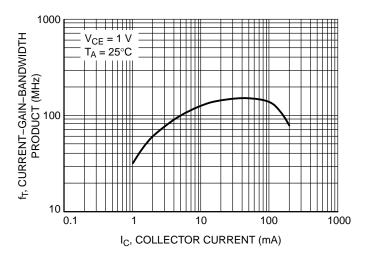


Figure 12. Current Gain Bandwidth Product vs. Collector Current

TYPICAL CHARACTERISTICS - BC807-25LT1

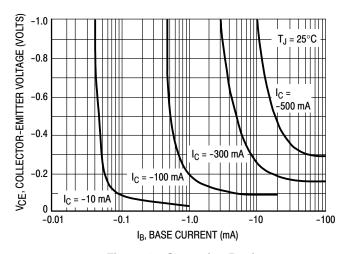


Figure 13. Saturation Region

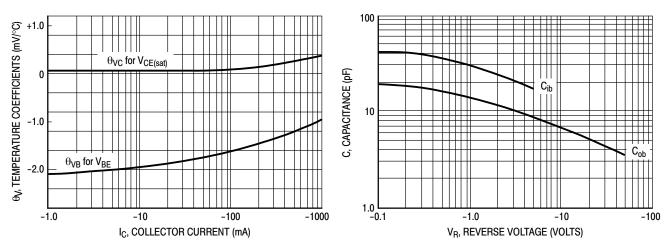


Figure 14. Temperature Coefficients

Figure 15. Capacitances

TYPICAL CHARACTERISTICS - BC807-40LT1

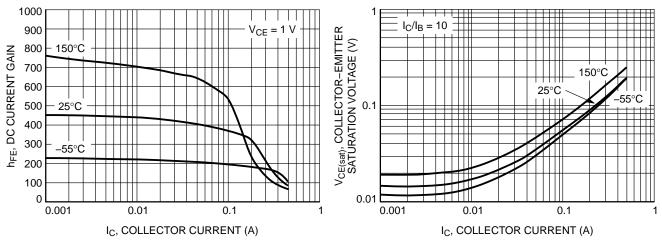


Figure 16. DC Current Gain vs. Collector Current

Figure 17. Collector Emitter Saturation Voltage vs. Collector Current

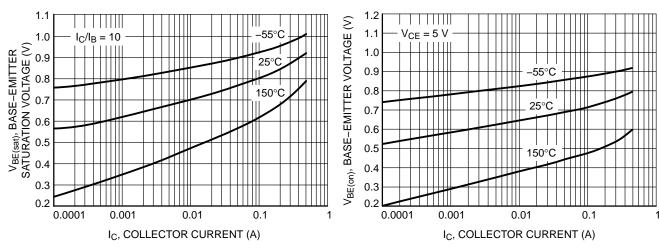


Figure 18. Base Emitter Saturation Voltage vs.
Collector Current

Figure 19. Base Emitter Voltage vs. Collector Current

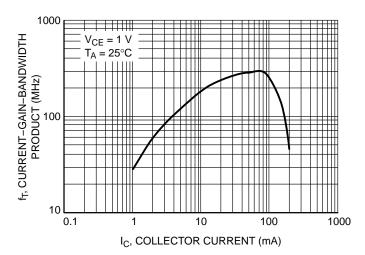


Figure 20. Current Gain Bandwidth Product vs. Collector Current

TYPICAL CHARACTERISTICS - BC807-40LT1

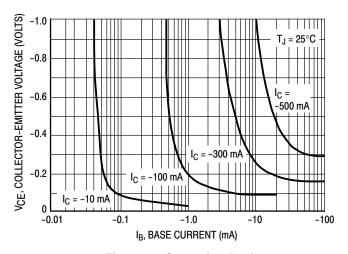


Figure 21. Saturation Region

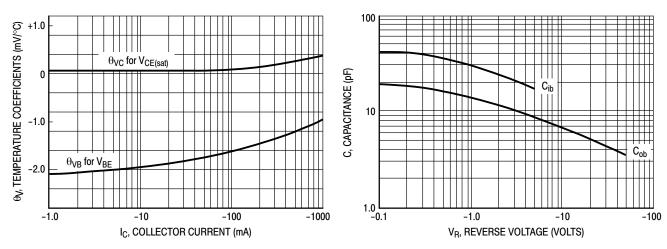


Figure 22. Temperature Coefficients

Figure 23. Capacitances

TYPICAL CHARACTERISTICS - BC807-16LT1, BC807-25LT1, BC807-40LT1

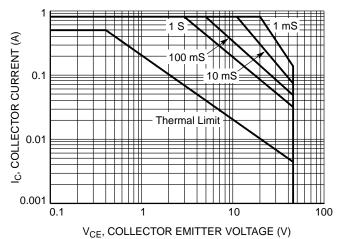


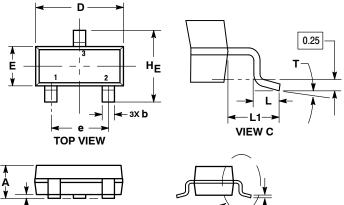
Figure 24. Safe Operating Area



SOT-23 (TO-236) CASE 318-08 **ISSUE AS**

DATE 30 JAN 2018

SCALE 4:1



SEE VIEW C

END VIEW

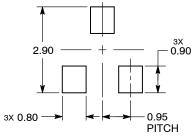
NOTES:

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH.
 MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH,
- PROTRUSIONS, OR GATE BURRS.

	M	ILLIMETE	RS		INCHES	
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	0.89 1.00 1.11 0.01 0.06 0.10 0.37 0.44 0.50 0.08 0.14 0.20 2.80 2.90 3.04 1.20 1.30 1.40		0.035	0.039	0.044
A1	0.01			0.000	0.002	0.004
b	0.37			0.015	0.017	0.020
С	0.08			0.003	0.006	0.008
D	2.80			0.110	0.114	0.120
E	1.20			0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.080
L	L 0.30 0.43 L1 0.35 0.54		0.55	0.012	0.017	0.022
L1			0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	O٥		100	O٥		10°

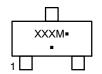
RECOMMENDED SOLDERING FOOTPRINT

SIDE VIEW



DIMENSIONS: MILLIMETERS

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code

= Date Code

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE
STVI F a	OTV/1 F 40:	OT/1 E 44	OT (1 5 40)

SOT-23 (TO-236)

STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12:	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. SOURCE	PIN 1. CATHODE
ANODE	SOURCE	CATHODE	CATHODE	2. DRAIN	2. GATE
CATHODE	GATE	CATHODE-ANODE	ANODE	GATE	ANODE

STYLE 1	5:	STYLE 1	6:	STYLE 1	7:	STYLE 1	8:	STYLE 1	19:	STYLE 2	20:
PIN 1.	GATE	PIN 1.	ANODE	PIN 1.	NO CONNECTION	PIN 1.	NO CONNECTION	PIN 1.	CATHODE	PIN 1.	CATHODE
2.	CATHODE	2.	CATHODE	2.	ANODE	2.	CATHODE	2.	ANODE	2.	ANODE
3.	ANODE	3.	CATHODE	3.	CATHODE	3.	ANODE	3.	CATHODE-ANODE	3.	GATE

STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
2. SOURCE	OUTPUT	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3 DRAIN	3 INPUT	3 CATHODE	3. SOURCE	3. GATE	3. NO CONNECTION

2. CATHODE 2.	28: . ANODE 2. ANODE 3. ANODE	
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